

1819AB25

25 Watts, 25 Volts, Class AB Personal 1808 - 1880 MHz

GENERAL DESCRIPTION

The 1819AB25 is a COMMON EMITTER transistor capable of providing 25 Watts of Class AB, RF output power over the band 1808-1880 MHz. This transistor is specifically designed for **PERSONAL COMMUNICATIONS BASE STATION** amplifier applications. It includes Input prematching and utilizes Gold metalization and HIGH VALUE EMITTER ballasting to provide high reliability and supreme ruggedness. .

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C 87 Watts

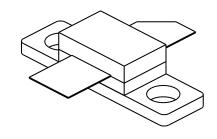
Maximum Voltage and Current

BVces Collector to Emitter Voltage 60Volts
BVebo Emitter to Base Voltage 3.5 Volts
Ic Collector Current 10.0 Amps

Maximum Temperatures

Storage Temperature $-65 \text{ to} + 150 ^{\circ}\text{C}$ Operating Junction Temperature $+200 ^{\circ}\text{C}$

CASE OUTLINE 55CT, STYLE 2 COMMON EMITTER



ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout Pin Pg η _c VSWR ₁	Power Out Power Input Power Gain Collector Efficiency Load Mismatch Tolerance	F=1880 MHz Vce = 25 Volts Icq = 0.27 Amps As Above	25 7.0	7.5 43	5.0	Watt Watt dB %

BVces BVebo Ices h _{FE} Cob	Collector to Emitter Breakdown Emitter to Base Breakdown Collector Leakage Current DC - Current Gain Output Capacitance Thormal Positiones	Ic = 50 mA Ie = 10 mA Vce = 27 Volts Vce = 5 V, Ic = 0.7 A F = 1 MHz, Vcb = 28 V	60 3.5 20	28	10 100	Volts Volts mA
θ jc	Thermal Resistance	$Tc = 25^{\circ}C$			2.0	°C/W

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